Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	0	("zerowithRFwithbias").PN.	USPAT; USOCR	OR	OFF	2005/04/27 07:47
S2	215	zero with RF with bias	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 08:03
S3	8	S2 with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 08:02
S4	0	RF with bias with rezo with charg$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 08:03
S5	7	RF with bias with zero with charg$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 08:07
S6	6	charg$4 with plasma with overetch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 08:10
S7	1	charg$4 with plasma with overetch with bias	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 08:10
S8	29239	charg$4 with bias	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 08:10
S9	49	S8 with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 08:23
S10	826	S8 with zero	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 08:23

S11	2	S10 with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 08:24
S12	52570	charg$4 with semiconduct$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 08:25
S13	11	S12 with RF with bias	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 08:36
S14	1174	RF with bias with power with MHz	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 08:36
S15	40	S14 with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 08:38
S16	9848	Rf with frequency with MHZ	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 08:41
S17	142	S16 with etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 08:55
S18	15	S17 with bias	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 08:39
S19	0	S17 with S2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 08:42
S20	1	S16 with S2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 08:42

S21	56	binary with lanthanum with oxid$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 08:57
S22	3283	high adj K with dielectric$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 08:58
S23	1432	S22 with gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 08:58
S24	1432	high adj K with gate with dielectric$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 09:00
S25	0	S24 with greater with than	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 08:59
S26	796	S24 with oxid$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 09:00
S27	3867185	S24 with oxid$3 samr consist$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 09:01
S28	58	S24 with oxid$3 same consist$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 09:12
S29	1638507	gate adj dielectri$3 with consist$4 with thermal$3 with high adj K or constant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 09:04
S30	33888	lanthanum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 09:13

S31	29	S30 and S28	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 09:26
S32	492	high adj K with constant same great$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 09:26
S33	91	S32 and lanthanum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 09:41
S34	86	hardmask with consist$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 09:42
S35	35	hardmask with consist$4 with silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 09:45
S36	13	hardmask with consist$4 with silicon with oxy$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 09:45

Title Details

Title:	High Density Plasma Sources - Design, Physics and Performance
Publisher:	William Andrew Publishing/Noyes
Copyright / Pub. Date:	© 1995
ISBN:	0-8155-1377-1
Electronic ISBN:	1-59124-063-8
No. Pages:	445
Author/Editor:	Edited by: Popov, O.A.
Knovel Release Date:	Feb 9, 2001
Description:	This book describes the design, physics, and performance of high density plasma sources which have been extensively explored in low pressure plasma processing, such as plasma etching and planarization, plasma enhanced chemical vapor deposition of thin films, sputtered deposition of metals and dielectrics, epitaxial growth of silicon and GaAs, and many other applications. This is a comprehensive survey and a detailed description of most advanced high density plasma sources used in plasma processing.